

Features

- Low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested

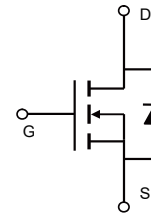
Product Summary

Parameter	Value	Unit
V_{DS}	60	V
$V_{GS(th)}_{Typ}$	1.8	V

(1)



DFN3x3



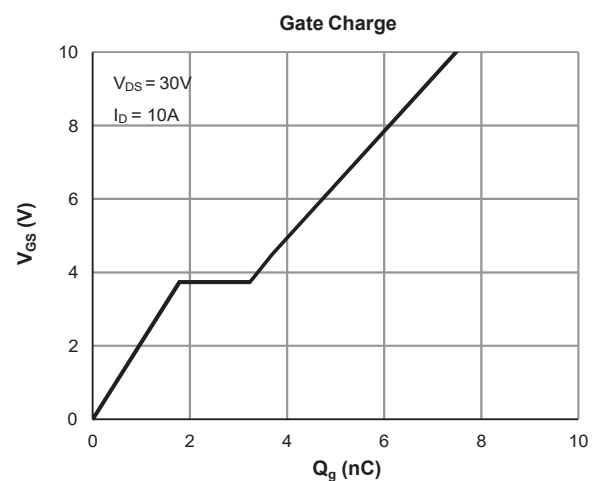
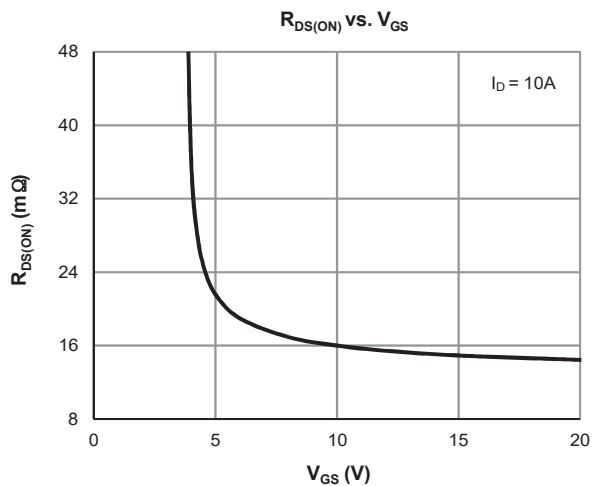
Schematic

Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
VSM24N06-D33	DFN3x3	8	VSM24N06	1	-55 to 150	13-inch Reel	5000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Human Body Model (per JESD22-A114)	V_{ESD_GS}	1.1	kV
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ\text{C}$	24
		$T_C = 100^\circ\text{C}$	15.4
Pulsed Drain Current ⁽²⁾	I_{DM}	47	A
Avalanche Energy ⁽³⁾	E_{AS}	26	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ\text{C}$	23
		$T_C = 100^\circ\text{C}$	9.1
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\text{V}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48\text{V}$, $V_{GS} = 0\text{V}$			1.0	μA
		$T_J = 55^\circ\text{C}$			5.0	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.2	1.8	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 10\text{A}$		16.0	20	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}$, $I_D = 8\text{A}$		23	30	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 10\text{A}$		14.6		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.73	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			23	A

DYNAMIC PARAMETERS ⁽⁵⁾

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 30\text{V}$, $f = 1\text{MHz}$		409		pF
Output Capacitance	C_{oss}			143		pF
Reverse Transfer Capacitance	C_{rss}			24		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		1.1		Ω

SWITCHING PARAMETERS ⁽⁵⁾

Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to -10V $V_{DS} = 30\text{V}$, $I_D = 10\text{A}$		7.5		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			3.7		nC
Gate Source Charge	Q_{gs}			1.8		nC
Gate Drain Charge	Q_{gd}			1.5		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 30\text{V}$ $R_L = 3\ \Omega$, $R_{GEN} = 6\ \Omega$		4.4		ns
Turn-On Rise Time	t_r			23		ns
Turn-Off DelayTime	$t_{D(off)}$			11.5		ns
Turn-Off Fall Time	t_f			3.2		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		15.2		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 10\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		5.4		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	R_{JA}	70	84	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	R_{JC}	5.5	6.6	$^\circ\text{C/W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 26 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3.0\text{mH}$, $I_{AS} = 4.2\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 30\text{V}$; 100% test at $L = 0.3\text{mH}$, $I_{AS} = 10\text{A}$.
 $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

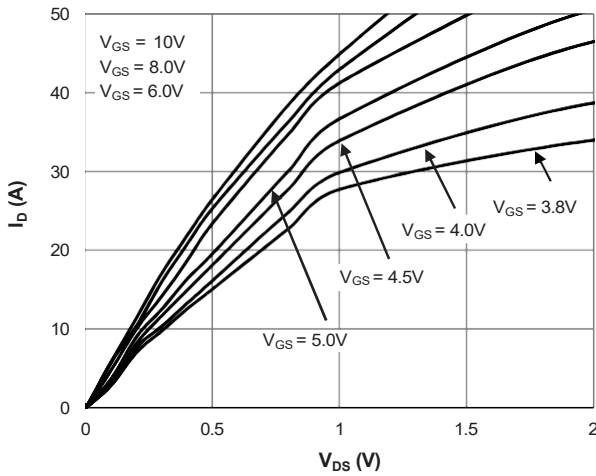


Figure 1: Saturation Characteristics

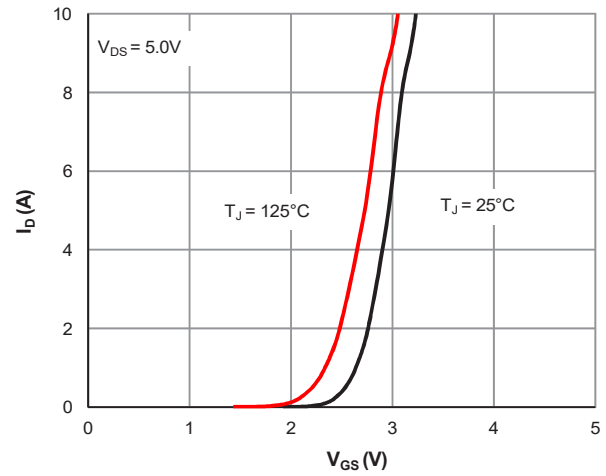


Figure 2: Transfer Characteristics

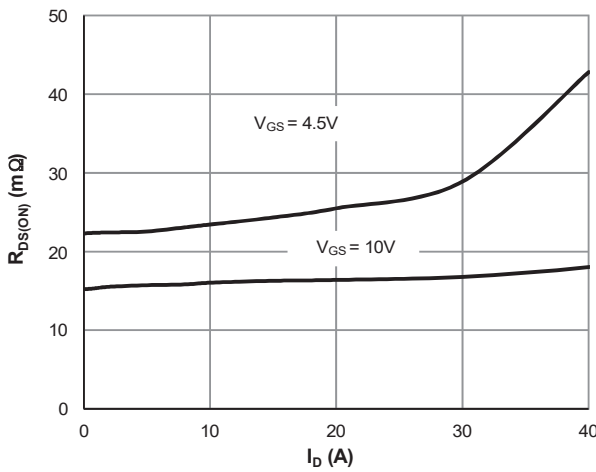


Figure 3: $R_{DS(ON)}$ vs. Drain Current

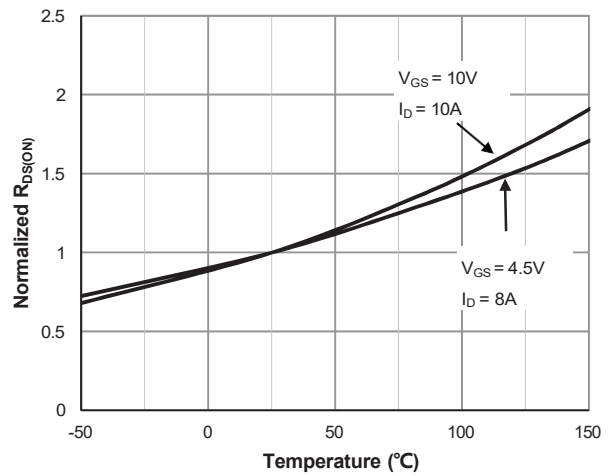


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

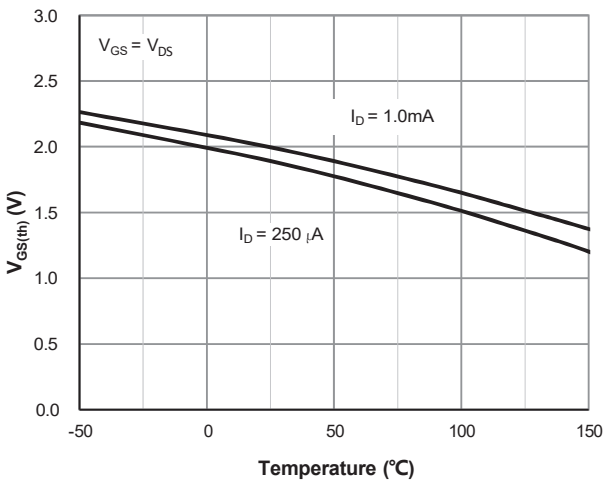


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

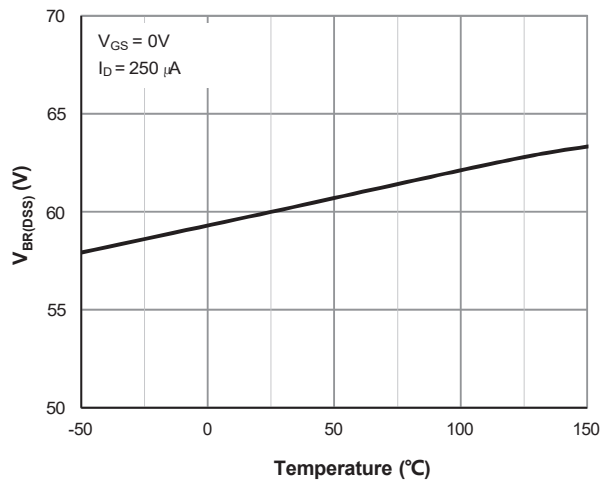


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

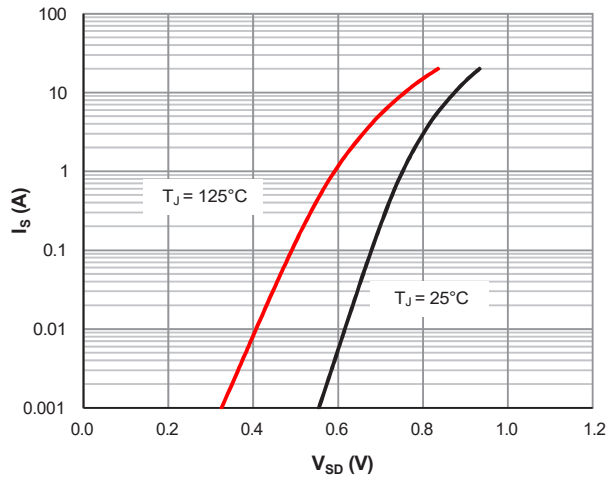


Figure 7: Body-Diode Characteristics

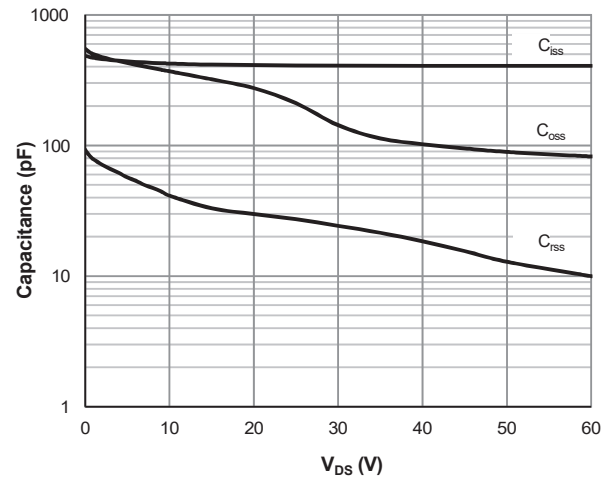


Figure 8: Capacitance Characteristics

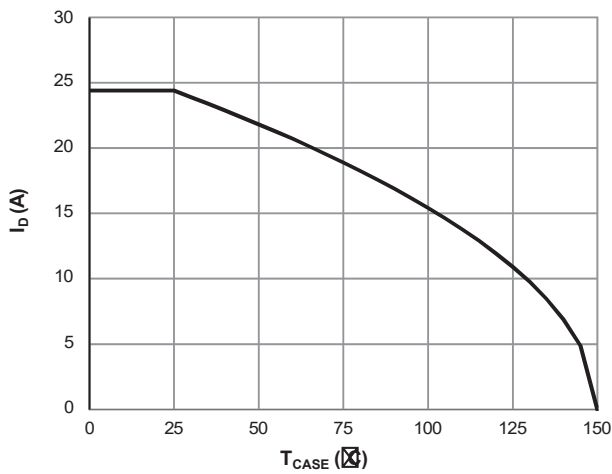


Figure 9: Current De-rating

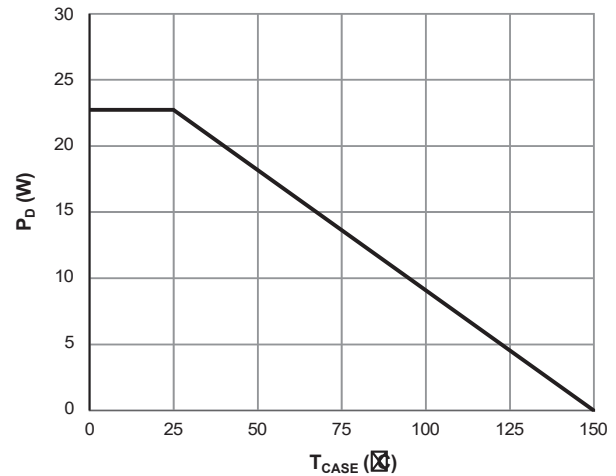


Figure 10: Power De-rating

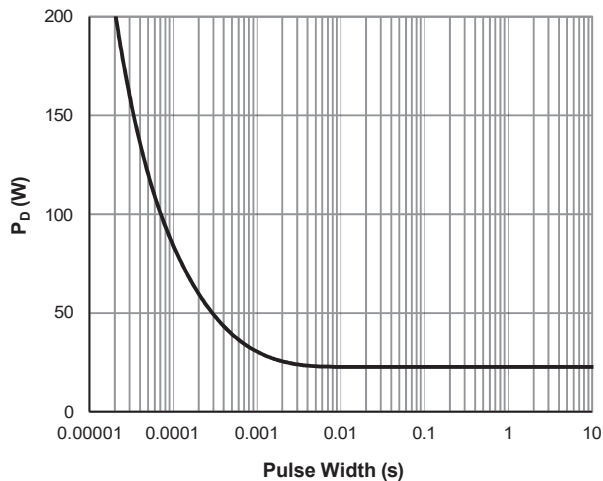


Figure 11: Single Pulse Power Rating, Junction-to-Case

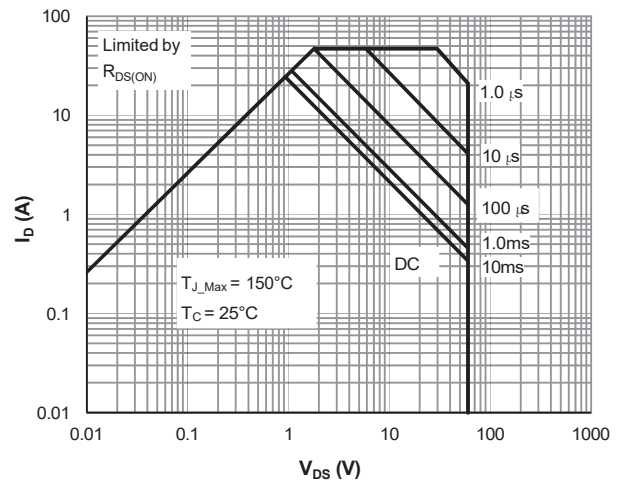


Figure 12: Maximum Safe Operating Area

Typical Electrical & Thermal Characteristics

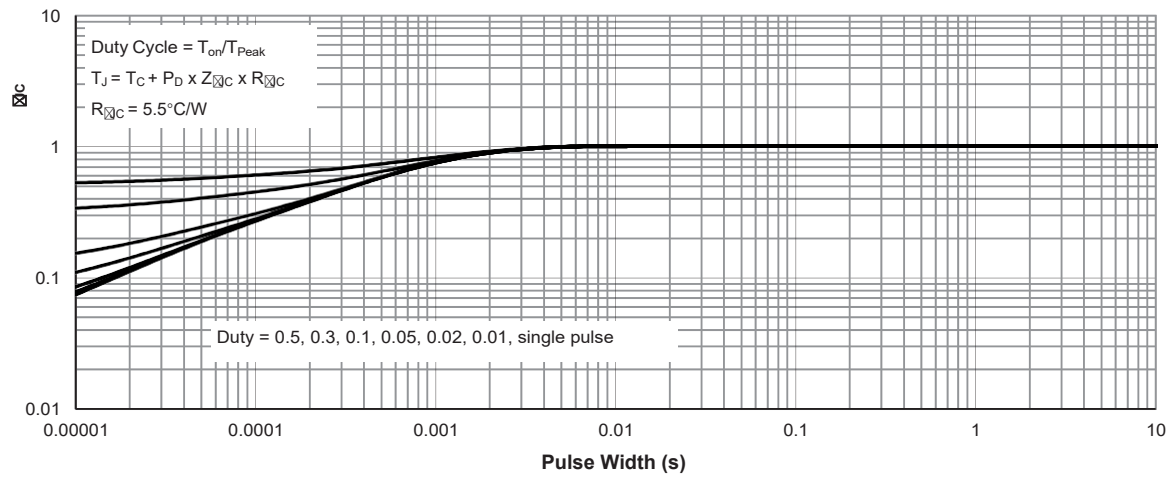


Figure 13: Normalized Maximum Transient Thermal Impedance